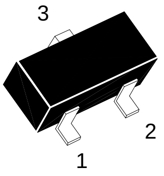
P-Channel Enhancement-Mode MOSFET (-30V, -4.3A)

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(on)}$ (m-ohm) Max
-30V	-4.3A	55 @ V_{GS} = -10 V,I_D=-4.3A
		78 @ V_{GS} = -4.5V,I_D=-3.0A

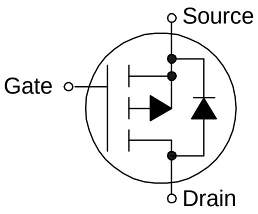
Features

- Super high dense cell trench design for low RDS(on).
- Rugged and reliable.
- SOT-23-3L package

KF3407 Pin Assignment & Symbol



3-Lead Plastic **SOT-23-3L**
Pin 1: Gate 2: Source 3: Drain



Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current @T_A=25°C[1,6]	-4.3	A
	Drain Current @T_A=70°C[1,6]	-3.5	
I_{DM}	Drain Current (Pulsed)[2]	-20	A
P_D	Total Power Dissipation @T_A=25°C[1]	1.4	W
	Total Power Dissipation @T_A=70°C[1]	0.9	
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient （Steady-State）[1]	125	°C/W
	Thermal Resistance Junction to Ambient （t⩽10S）[1,6]	90	
$R_{\theta JL}$	Maximum Junction-to-Lead[3]	80	°C/W